

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
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JUN 26 2003

37 CFR 1.98(b)

APPLICANT
Atsushi YAMAGUCHI et al.FILING DATE
September 4, 2001GROUP
2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA						

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

		DOCUMENT NO.	PUBL. DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION YES - NO
<i>SL</i>	AI	A 11-307866	11/99	JP			with English abstract
<i>SL</i>	AJ	A 11-340580	12/99	JP			with English abstract
	AK						

OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication)

<i>SL</i>	AL	Shuji NAKAMURA, "Current Status and Future Prospects of InGaN-Based Laser Diodes," JSAP International, Jan. 2000, Tokushima, Japan, pp. 5-17.
<i>SL</i>	AM	Masaru KURAMOTO et al., "Towards a Durable InGaN MQW LD--Room Temperature CW Operation of InGaN MQW Laser," NEC Res. & Develop., V. 41, January 2000, pp. 74-86.
<i>SL</i>	AN	Shuji NAKAMURA et al., "InGaN/GaN/AlGaN-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices," Jpn. J. Appl. Phys., V. 36, 1997, pp. L1568-L1571.
<i>SL</i>	AO	Akira USUI et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy," Jpn. J. Appl. Phys., V. 36, 1997, pp. L899-L902.
<i>SL</i>	AP	Shigefusa CHICHIBU, "Spatially Resolved Cathodoluminescence Spectra of InGaN Quantum Wells," Appl. Phys. Lett. 71, 1997, pp. 2346-2348.
<i>SL</i>	AQ	W. W. CHOW et al., "Microscopic Theory of Gain for an InGaN/AlGaN Quantum Well Laser," Appl. Phys. Lett. 71, 1997, pp. 2608-2610.
<i>SL</i>	AR	A. Atsushi YAMAGUCHI et al., "Optical Recombination Processes in High-Quality GaN Films and InGaN Quantum Wells Grown on Facet-Initiated Epitaxial Lateral Overgrown GaN Substrates," Jpn. J. Appl. Phys., V. 39, 2000, pp. 2402-2406.
<i>SL</i>	AS	G. Martin et al., "Valence-Band Discontinuities of Wurtzite GaN, AlN, and InN. Heterojunctions Measured by X-Ray Photoemission Spectroscopy," Appl. Phys. Lett. 68, 1996, pp. 2541-2543.
	AT	

EXAMINER

Shoumeej SL

DATE CONSIDERED

2-19-04

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered.
Include copy of this form with next communication to applicant.